

Figure 1. Thickness versus time QCM measurements for Si (no native oxide) vs SiO₂ at (a) 50 °C and (b) 40 °C. (c) Si with native oxide versus SiO₂ at 45 °C. (d) expanded view of the region in the red box in (c). Plasma conditions: NF₃:NH₃:Ar = 1:10:1.5 190mTorr 100W.

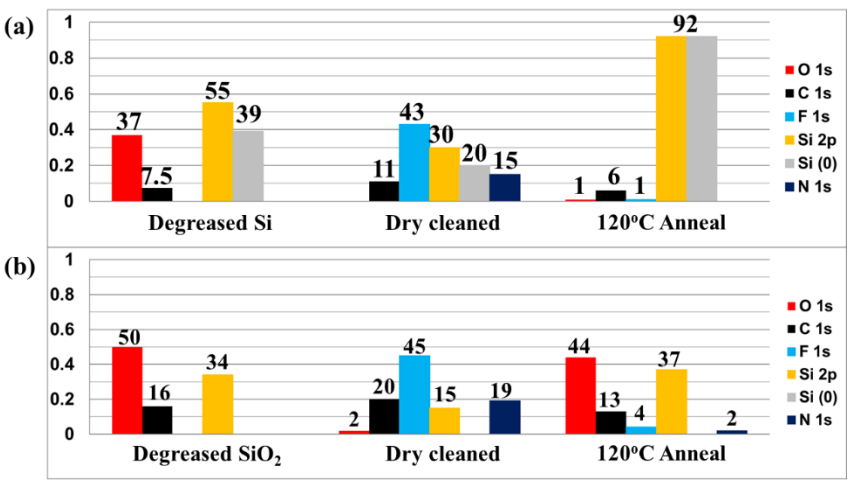


Figure 2. XPS elemental composition data for (a) Si and (b) SiO₂ before dry clean, after dry clean, and after a 120 °C anneal for 30 minutes. Values are normalized to the sum of O + C + F + Si + N.

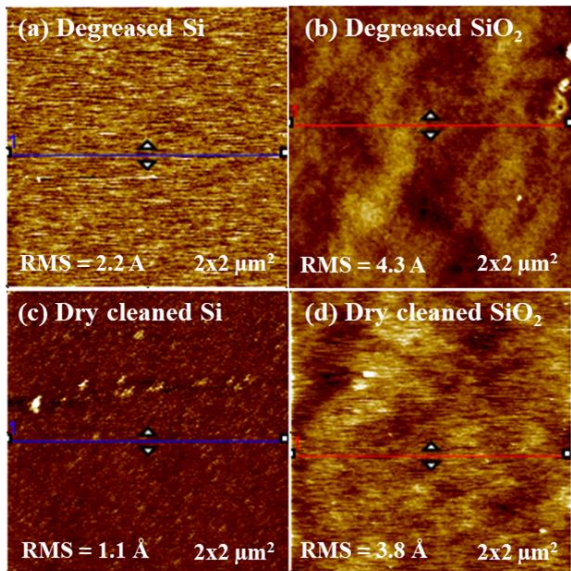


Figure 3. AFM images of (a) degreased Si, (b) degreased SiO₂, (c) dry cleaned Si and (d) dry cleaned SiO₂. RMS roughness values were calculated averaging over the entire image.